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**1N746
THRU
1N759**

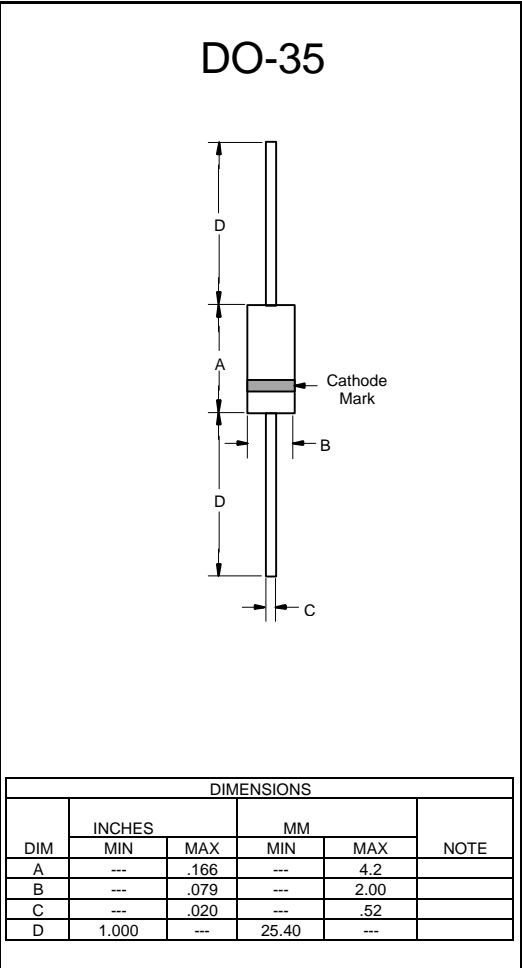
Features

- Zener Voltage 3.3V to 12V
- Silicon Planar Power Zener Diodes
- Standards zener voltage tolerance is $\pm 10\%$, Add suffix "A" for $\pm 5\%$ tolerance, other tolerances are available upon request

**0.5W Silicon Planar
Zener Diodes**

Mechanical Data

- Case: DO-35 glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13 gram



Maximum Ratings

	Symbol	Value	Units
Zener Current		See Table 1	
Power Dissipation @ $T_A=50^\circ\text{C}$	P_{tot}	500	mW
Junction Temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to 175	$^\circ\text{C}$

Electrical Characteristics @ 25°C Unless Otherwise Specified

	Symbol	Maximum	Unit
Thermal resistance	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Forward Voltage @ $I_F=200\text{mA}$	V_F	1.5	V

NOTE:

- 1) Valid provided that a distance of 8mm from case are kept at ambient temperature
- 2) Power derating: 4.0mW/ $^\circ\text{C}$ above 50 $^\circ\text{C}$

1N746 thru 1N759



PART NUMBER	NORMAL ZENER VOLTAGE $V_z @ I_{zt}$	TEST CURRENT I_{zt}	MAXIMUM ZENER IMPEDANCE $Z_{zt} @ I_{zt}$	MAXIMUM REVERSE LEAKAGE CURRENT $I_r @ V_r=1V$		MAXIMUM ZENER CURRENT I_{zm}	TYPICAL TEMP. COEFFICIENT
	VOLTS	mA	OHMS	uA @25°C	uA @125°C	mA	%/°C
1N746	3.3	20	28	10	30	110	-.066
1N747	3.6	20	24	10	30	100	-.058
1N748	3.9	20	23	10	30	95	-.046
1N749	4.3	20	22	2	30	85	-.033
1N750	4.7	20	19	2	30	75	-.015
1N751	5.1	20	17	1	20	70	±.010
1N752	5.6	20	11	1	20	65	+.030
1N753	6.2	20	7.0	0.1	20	60	+.049
1N754	6.8	20	5.0	0.1	20	55	+.053
1N755	7.5	20	6.0	0.1	20	50	+.057
1N756	8.2	20	8.0	0.1	20	45	+.060
1N757	9.1	20	10	0.1	20	40	+.061
1N758	10	20	17	0.1	20	35	+.062
1N759	12	20	30	0.1	20	30	+.062

Note:

- 1) Tested with pulses $t_p=20ms$
- 2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.
- 3) Zener impedance derived by superimposing on I_{zT} , a 60 cps, rms ac current equal to 10% I_{zT} (2 mA ac)
- 4) Allowance has been made for the increase in V_z due to Z_z and for the increase in junction temperature as the unit approaches thermal equilibrium at the power dissipation of 400mW.